

PUMD15-Q

50 V, 100 mA NPN/PNP resistor-equipped double transistor; R1 = 4.7 k Ω , R2 = 4.7 k Ω

8 March 2023

Product data sheet

1. General description

NPN/PNP double Resistor-Equipped Transistor (RET) in a very small SOT363 (SC-88) Surface-Mounted Device (SMD) plastic package.

NPN/NPN complement: PUMH15 PNP/PNP complement: PUMB15

2. Features and benefits

- 100 mA output current capability
- Built-in bias resistors
- Simplified circuit design
- · Reduces component count
- Reduces pick and place costs
- Qualified according to AEC-Q101 and recommended for use in automotive applications

3. Applications

- Low current peripheral driver
- Controlling IC inputs
- · Replacement of general purpose transistors in digital applications

4. Quick reference data

Table 1. Quick reference data

Table II Quiek Telefolie auta								
Symbol	Parameter	Conditions		Min	Тур	Max	Unit	
Per transistor						<u>'</u>		
V _{CEO}	collector-emitter voltage	open base	[1]	-	-	50	V	
Io	output current		[1]	-	-	100	mA	
R1	bias resistor 1 (input)		[2]	3.3	4.7	6.1	kΩ	
R2/R1	bias resistor ratio		[2]	0.8	1	1.2		

- [1] For the PNP transistor (TR2) with negative polarity.
- [2] See section "Test information" for resistor calculation and test conditions.



50 V, 100 mA NPN/PNP resistor-equipped double transistor; R1 = 4.7 k Ω , R2 = 4.7 k Ω

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	GND1	GND (emitter) TR1		O1 I2 GND2
2	I1	input (base) TR1		
3	O2	output (collector) TR2	6 5 4	R1 R2
4	GND2	GND (emitter) TR2		TR2
5	12	input (base) TR2		TR1 R2 R1
6	01	output (collector) TR1	☐1 ☐2 ☐3 TSSOP6 (SOT363)	GND1 I1 O2 006aaa143

6. Ordering information

Table 3. Ordering information

Type number	Package	Package						
	Name	Description	Version					
PUMD15-Q		plastic, surface-mounted package; 6 leads; 0.65 mm pitch; 2.1 mm x 1.25 mm x 0.95 mm body	<u>SOT363</u>					

7. Marking

Table 4. Marking codes

Type number	Marking code[1]
PUMD15-Q	D0%

[1] % = placeholder for manufacturing site code

50 V, 100 mA NPN/PNP resistor-equipped double transistor; R1 = 4.7 k Ω , R2 = 4.7 k Ω

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
Per transisto	or		,			
V _{CBO}	collector-base voltage	open emitter	[1]	-	50	V
V_{CEO}	collector-emitter voltage	open base	[1]	-	50	V
V_{EBO}	emitter-base voltage	open collector	[1]	-	10	V
V _I	input voltage	TR1 (NPN)		-10	30	V
		TR2 (PNP)		-30	10	V
Io	output current		[1]	-	100	mA
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	[2]	-	200	mW
Per device				'		
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	[2]	-	300	mW
Tj	junction temperature			-	150	°C
T _{amb}	ambient temperature			-65	150	°C
T _{stg}	storage temperature			-65	150	°C

- [1] For the PNP transistor (TR2) with negative polarity.
- [2] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

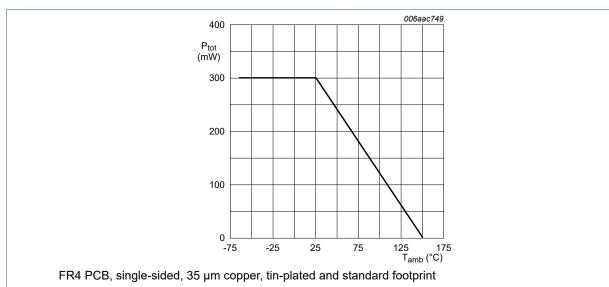


Fig. 1. Per device: Power derating curve

50 V, 100 mA NPN/PNP resistor-equipped double transistor; R1 = 4.7 k Ω , R2 = 4.7 k Ω

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Per transistor							
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	[1]	-	-	625	K/W
Per device							
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	[1]	-	-	417	K/W

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

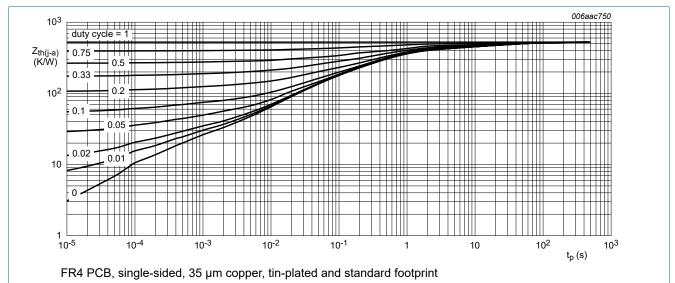


Fig. 2. Per transistor: Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

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50 V, 100 mA NPN/PNP resistor-equipped double transistor; R1 = 4.7 k Ω , R2 = 4.7 k Ω

10. Characteristics

Table 7. Characteristics

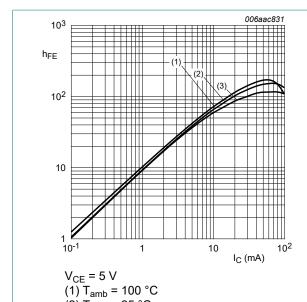
	Conditions		Min	Тур	Max	Unit
or						
collector-base breakdown voltage	$I_C = 100 \ \mu A; I_E = 0 \ A; T_{amb} = 25 \ ^{\circ}C$	[1]	50	-	-	V
collector-emitter breakdown voltage	$I_C = 2 \text{ mA}; I_B = 0 \text{ A}; T_{amb} = 25 ^{\circ}\text{C}$	[1]	50	-	-	V
collector-base cut-off current	V _{CB} = 50 V; I _E = 0 A; T _{amb} = 25 °C	[1]	-	-	100	nA
collector-emitter cut-off	V _{CE} = 30 V; I _B = 0 A; T _{amb} = 25 °C	[1]	-	-	100	nA
current	V _{CE} = 30 V; I _B = 0 A; T _j = 150 °C	[1]	-	-	5	μΑ
emitter-base cut-off current	$V_{EB} = 5 \text{ V}; I_{C} = 0 \text{ A}; T_{amb} = 25 \text{ °C}$	[1]	-	-	900	μΑ
DC current gain	V _{CE} = 5 V; I _C = 10 mA; T _{amb} = 25 °C	[1]	30	-	-	
collector-emitter saturation voltage	I_C = 10 mA; I_B = 0.5 mA; T_{amb} = 25 °C	[1]	-	-	150	mV
off-state input voltage	V _{CE} = 5 V; I _C = 100 μA; T _{amb} = 25 °C	[1]	-	1.1	0.5	V
on-state input voltage	V _{CE} = 0.3 V; I _C = 20 mA; T _{amb} = 25 °C	[1]	2.5	1.9	-	V
bias resistor 1 (input)		[2]	3.3	4.7	6.1	kΩ
bias resistor ratio		[2]	0.8	1	1.2	
collector capacitance	$V_{CB} = 10 \text{ V}; I_E = 0 \text{ A}; i_e = 0 \text{ A}; f = 1 \text{ MHz}; T_{amb} = 25 ^{\circ}\text{C}$		-	-	2.5	pF
transition frequency	$V_{CE} = 5 \text{ V}; I_{C} = 10 \text{ mA}; f = 100 \text{ MHz};$ $T_{amb} = 25 \text{ °C}$	[3]	-	230	-	MHz
			'			
collector capacitance	$V_{CB} = -10 \text{ V}; I_E = 0 \text{ A}; i_e = 0 \text{ A};$ f = 1 MHz; $T_{amb} = 25 \text{ °C}$		-	-	3	pF
transition frequency	V_{CE} = -5 V; I_{C} = -10 mA; f = 100 MHz; T_{amb} = 25 °C	[3]	-	180	-	MHz
	collector-base breakdown voltage collector-emitter breakdown voltage collector-base cut-off current collector-emitter cut-off current emitter-base cut-off current DC current gain collector-emitter saturation voltage off-state input voltage on-state input voltage bias resistor 1 (input) bias resistor ratio collector capacitance transition frequency	collector-base breakdown voltage	collector-base breakdown voltage	collector-base breakdown voltage $I_C = 100 \mu A; I_E = 0 A; T_{amb} = 25 ^{\circ}C$ [1] 50 collector-emitter breakdown voltage $I_C = 2 mA; I_B = 0 A; T_{amb} = 25 ^{\circ}C$ [1] 50 collector-emitter breakdown voltage $V_{CB} = 50 V; I_E = 0 A; T_{amb} = 25 ^{\circ}C$ [1] - collector-base cut-off current $V_{CE} = 30 V; I_B = 0 A; T_{amb} = 25 ^{\circ}C$ [1] - collector-emitter cut-off current $V_{CE} = 30 V; I_B = 0 A; T_{amb} = 25 ^{\circ}C$ [1] - emitter-base cut-off current $V_{CE} = 30 V; I_C = 0 A; T_{amb} = 25 ^{\circ}C$ [1] - DC current gain $V_{CE} = 5 V; I_C = 10 mA; T_{amb} = 25 ^{\circ}C$ [1] - collector-emitter saturation voltage $I_C = 10 mA; I_B = 0.5 mA; T_{amb} = 25 ^{\circ}C$ [1] - off-state input voltage $V_{CE} = 5 V; I_C = 100 \mu A; T_{amb} = 25 ^{\circ}C$ [1] - on-state input voltage $V_{CE} = 5 V; I_C = 20 mA; T_{amb} = 25 ^{\circ}C$ [1] 2.5 bias resistor 1 (input) [2] 3.3 bias resistor ratio [2] 0.8 collector capac	collector-base breakdown voltage $I_C = 100 \mu A; I_E = 0 A; T_{amb} = 25 ^{\circ}C$ [1] 50 - collector-emitter breakdown voltage $I_C = 2 \text{mA}; I_B = 0 A; T_{amb} = 25 ^{\circ}C$ [1] 50 - collector-base cut-off current $V_{CB} = 50 V; I_E = 0 A; T_{amb} = 25 ^{\circ}C$ [1] - - collector-emitter cut-off current $V_{CE} = 30 V; I_B = 0 A; T_{amb} = 25 ^{\circ}C$ [1] - - emitter-base cut-off current $V_{CE} = 30 V; I_B = 0 A; T_{amb} = 25 ^{\circ}C$ [1] - - DC current gain $V_{CE} = 5 V; I_C = 10 \text{mA}; T_{amb} = 25 ^{\circ}C$ [1] - - collector-emitter saturation voltage $I_C = 10 \text{mA}; I_B = 0.5 \text{mA}; T_{amb} = 25 ^{\circ}C$ [1] - - off-state input voltage $V_{CE} = 5 V; I_C = 100 \mu A; T_{amb} = 25 ^{\circ}C$ [1] - - on-state input voltage $V_{CE} = 5 V; I_C = 100 \mu A; T_{amb} = 25 ^{\circ}C$ [1] - 1.1 bias resistor 1 (input) [2] 3.3 4.7 bias resistor ratio $V_{CB} = 10 V; I_C = 10 MA; I_C = 0 A; I_C $	$ \begin{array}{ c c c c c c c c c c c c c c c c c c c$

^[1] For the PNP transistor (TR2) with negative polarity.

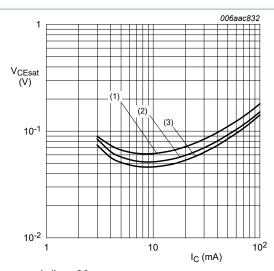
^[2] See section "Test information" for resistor calculation and test conditions.

^[3] Characteristics of built-in transistor

50 V, 100 mA NPN/PNP resistor-equipped double transistor; R1 = 4.7 k Ω , R2 = 4.7 k Ω



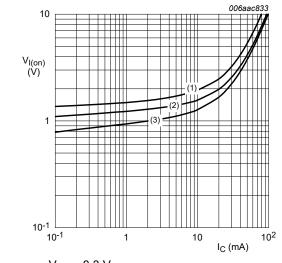
(2) T_{amb} = 25 °C (3) T_{amb} = -40 °C TR1 (NPN): DC current gain as a function of Fig. 3. collector current; typical values



$$I_{C}/I_{B} = 20$$
(1) $T_{amb} = 100 \,^{\circ}C$
(2) $T_{amb} = 25 \,^{\circ}C$
(3) $T_{amb} = -40 \,^{\circ}C$

(3)
$$T_{amb} = -40 \, ^{\circ}C$$

Fig. 4. TR1 (NPN): Collector-emitter saturation voltage as a function of collector current; typical values

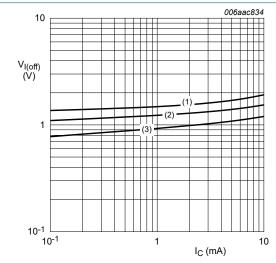


 $V_{CE} = 0.3 V$ (1) T_{amb} = -40 °C

(2) $T_{amb} = 25 \, ^{\circ}C$

(3) T_{amb} = 100 °C





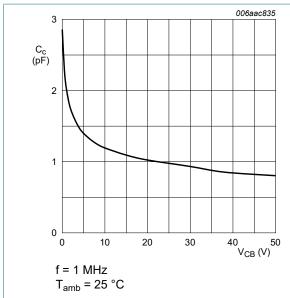
 $V_{CE} = 5 V$ (1) $T_{amb} = -40 \, ^{\circ}C$

(2) $T_{amb} = 25 \, ^{\circ}C$

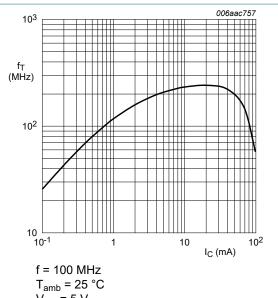
(3) $T_{amb} = 100 \, ^{\circ}C$

TR1 (NPN): Off-state input voltage as a function of collector current; typical values

50 V, 100 mA NPN/PNP resistor-equipped double transistor; R1 = 4.7 k Ω , R2 = 4.7 k Ω

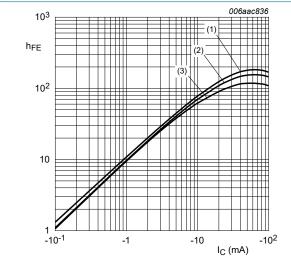


TR1 (NPN): Collector capacitance as a function Fig. 7. of collector-base voltage; typical values



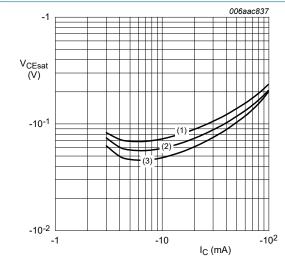
 T_{amb} = 25 °C V_{CE} = 5 V

TR1 (NPN): Transition frequency as a function Fig. 8. of collector current; typical values of built-in transistor



 V_{CE} = -5 V(1) $T_{amb} = 100 \, ^{\circ}C$ (2) T_{amb} = 25 °C (3) T_{amb} = -40 °C

Fig. 9. TR2 (PNP): DC current gain as a function of collector current; typical values



 $I_{\rm C}/I_{\rm B} = 20$ (1) T_{amb} = 100 °C (2) $T_{amb} = 25 \, ^{\circ}C$ (3) $T_{amb} = -40 \, ^{\circ}C$

Fig. 10. TR2 (PNP): Collector-emitter saturation voltage as a function of collector current; typical values

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50 V, 100 mA NPN/PNP resistor-equipped double transistor; R1 = 4.7 k Ω , R2 = 4.7 k Ω

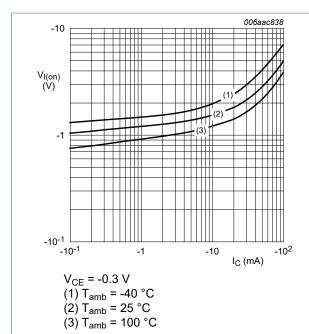
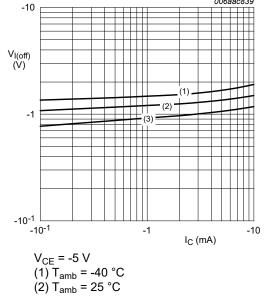


Fig. 11. TR2 (PNP): On-state input voltage as a function | Fig. 12. TR2 (PNP): Off-state input voltage as a function of collector current; typical values



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(3) $T_{amb} = 100 \, ^{\circ}C$



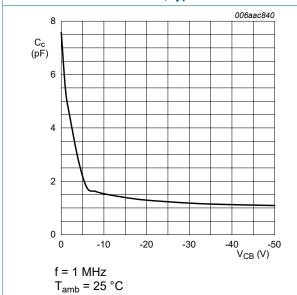
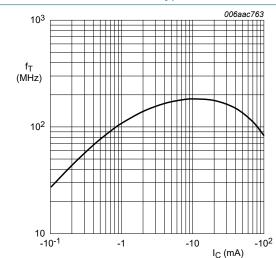


Fig. 13. TR2 (PNP): Collector capacitance as a function of collector-base voltage; typical values



f = 100 MHz T_{amb} = 25 °C $V_{CE} = -5 V$

Fig. 14. TR2 (PNP): Transition frequency as a function of collector current; typical values of built-in transistor

50 V, 100 mA NPN/PNP resistor-equipped double transistor; R1 = 4.7 k Ω , R2 = 4.7 k Ω

11. Test information

Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101* - *Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

Resistor calculation

· Calculation of bias resistor 1 (R1)

$$R_{I} = \frac{V(I_{2}) - V(I_{I})}{I_{2} - I_{I}}$$

· Calculation of bias resistor ratio (R2/R1)

$$\frac{R2}{R1} = \frac{V(I4) - V(I3)}{R1 \cdot (I4 - I3)} - 1$$

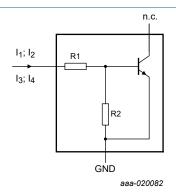


Fig. 15. NPN transistor: Resistor test circuit

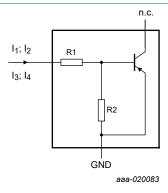


Fig. 16. PNP transistor: Resistor test circuit

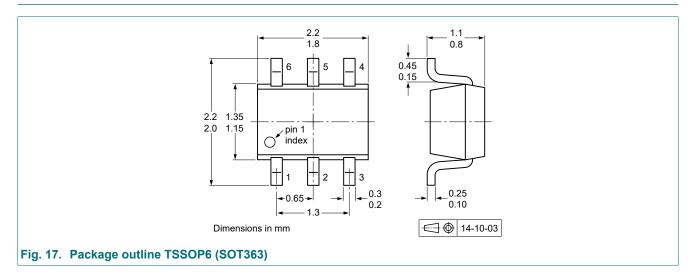
Resistor test conditions

Table 8. Resistor test conditions

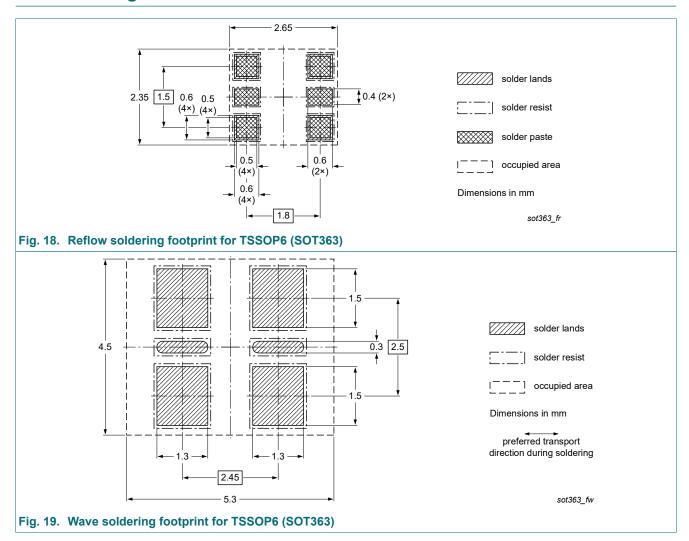
PUMD15-Q	R1 (kΩ)	R2 (kΩ)	Test conditions			
			I ₁	l ₂	l ₃	14
TR1 (NPN)	4.7	4.7	600 μΑ	700 μΑ	-600 μΑ	-700 μA
TR2 (PNP)	4.7	4.7	-600 μΑ	-700 μA	600 μΑ	700 µA

50 V, 100 mA NPN/PNP resistor-equipped double transistor; R1 = 4.7 k Ω , R2 = 4.7 k Ω

12. Package outline



13. Soldering



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50 V, 100 mA NPN/PNP resistor-equipped double transistor; R1 = 4.7 k Ω , R2 = 4.7 k Ω

14. Revision history

Table 9. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PUMD15-Q v.1	20230308	Product data sheet	-	-

50 V, 100 mA NPN/PNP resistor-equipped double transistor; R1 = 4.7 k Ω , R2 = 4.7 k Ω

15. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- Please consult the most recently issued document before initiating or completing a design.
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PUMD15-Q

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For sales office addresses, please send an email to: salesaddresses@nexperia.com
Date of release: 8 March 2023

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